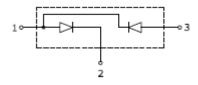


PRELIMINARY DATASHEET

Rectifier Diodes, 2 x 100A, 1600V, Half-Bridge Configuration In iQPak™ Power Module Package

- High voltage
- High surge capability
- Low thermal resistance
- Industrial standard package





MAXIMUM RATINGS (per Diode), at T_j = 25°C, unless otherwise specified

Parameter	Symbol	Value	Units
Repetitive peak reverse voltage	V _{RRM}	1600	٧
Average forward current T _C = 100°C	I _{F(AV)}	100	
Maximum RMS forward current	I _{F(RMS)}	157	Α
Surge non-repetitive forward current $t_p = 10$ ms, no voltage reapplied, half sine wave	I _{FSM}	2020	
Soldering temperature Wave soldering, 1.6 mm (0.063 in.) from case for 10s	Ts	260	°C
Operating junction and storage temperature	T _j , T _{stg}	-40 +150	

Thermal and Isolation Characteristics

Parameter	Symbol	Max. Value	Units
Characteristics			
Thermal resistance, junction to case, per Diode	R _{thJC}	0.22	°C/W
Isolation voltage, RMS (measured between terminals and mounting base, 50-60 Hz, for 1-3 seconds)	V_{iso}	3000	٧

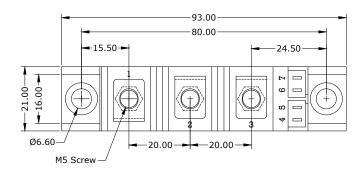
Electrical Characteristics (per Diode), at T_i = 25°C, unless otherwise specified

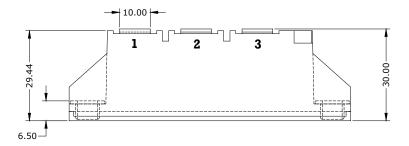
Parameter	Symbol	Value			Heit
		Min.	Тур.	Max.	Unit
Static Characteristics					
Reverse leakage current $V_R = 1600V$	I _R	-	-	10	mA
Forward voltage drop I _F = 100A	V _F	-	1.55	-	V

Revised: 17-Dec-12



Package Outline Drawing





Disclaimer

These specifications may not be considered as a guarantee of components characteristics. Components have to be tested depending on intended application as adjustments may be necessary. The use of **iQXPRZ Power Inc.** components in life support appliances and systems are subject to written approval of **iQXPRZ Power Inc.**

Revised: 17-Dec-12